

NPN SILICON EPITAXIAL TRANSISTOR
MP-3

DESCRIPTION

2SD1286-Z is designed for Switching, especially in Hybrid Integrate Circuits.

FEATURES

- High h_{FE} : $h_{FE} = 2\ 000$ to $30\ 000$
- Complement to 2SB963-Z

QUALITY GRADE

Standard

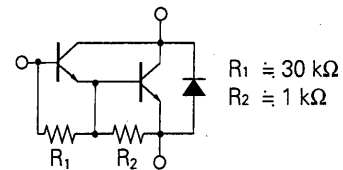
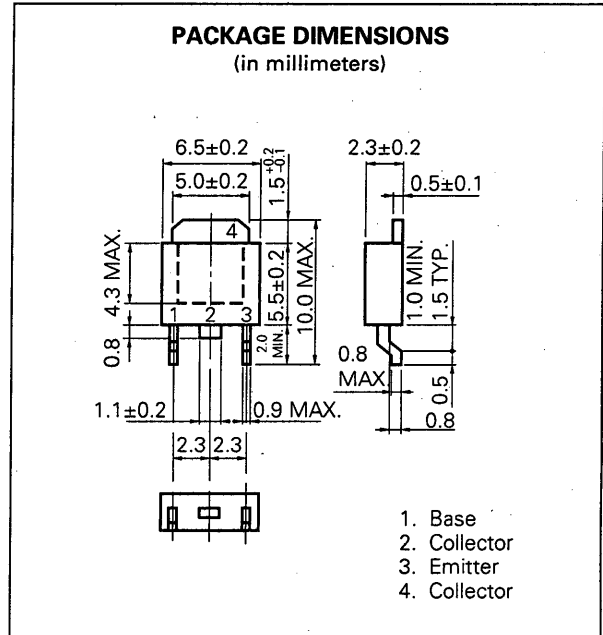
Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25\ ^\circ\text{C}$)

Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	60	V
Emitter to Base Voltage	V_{EBO}	8	V
Collector Current (DC)	I_C	1	A
Collector Current (Pulse)*	I_C	2	A
Total Power Dissipation ($T_a = 25\ ^\circ\text{C}$)**	P_T	2.0	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* $PW \leq 10\ \text{ms}$, Duty Cycle $\leq 50\ \%$

** When mounted on ceramic substrate of $7.5\ \text{cm}^2 \times 0.7\ \text{mm}$



ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

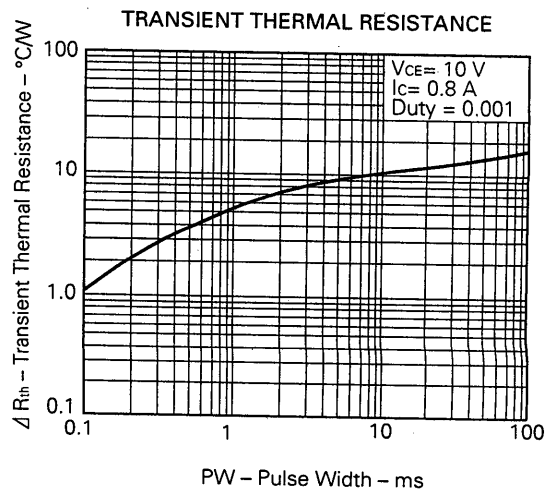
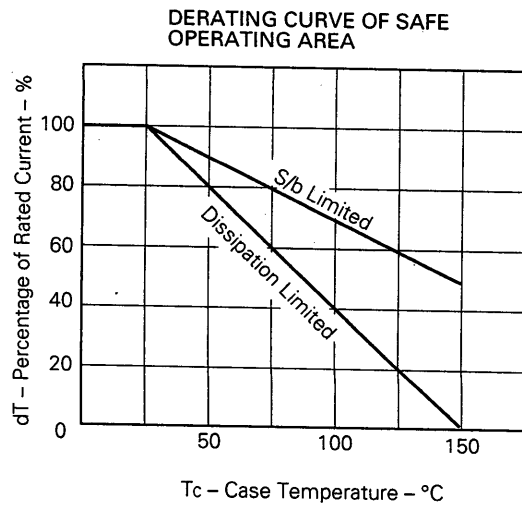
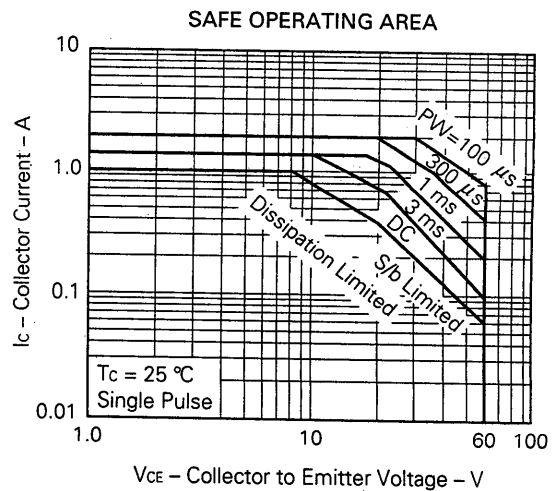
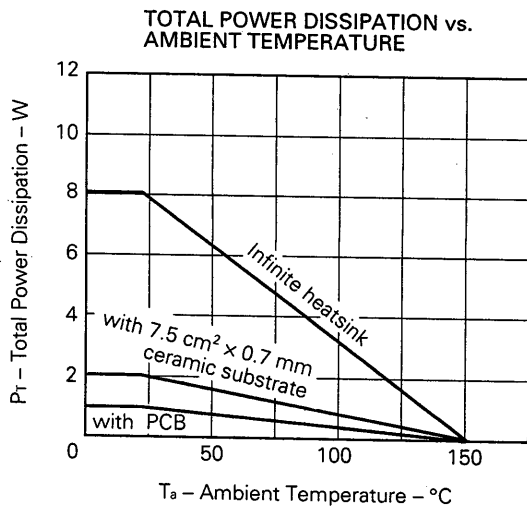
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	I _{CB0}			10	μA	V _{CB} = 60 V, I _E = 0
Emitter Cutoff Current	I _{EB0}			1.0	mA	V _{EB} = 5.0 V, I _C = 0
DC Current Gain	h _{FE1} *	1 000				V _{CE} = 2.0 V, I _C = 0.2 A
DC Current Gain	h _{FE2} *	2 000		30 000		V _{CE} = 2.0 V, I _C = 0.5 A
Collector Saturation Voltage	V _{CE(sat)} *			1.5	V	I _C = 500 mA, I _B = 0.5 mA
Base Saturation Voltage	V _{BE(sat)} *			2.0	V	I _C = 500 mA, I _B = 0.5 mA
Turn-on Time	t _{on}		0.5		μs	I _C = 0.5 A, R _L = 100 Ω I _{B1} = -I _{B2} = 0.1 mA V _{CC} = 50 V
Storage Time	t _{stg}		1.0		μs	
Fall Time	t _f		1.0		μs	

* Pulsed: PW ≤ 350 μs, Duty Cycle ≤ 2 %

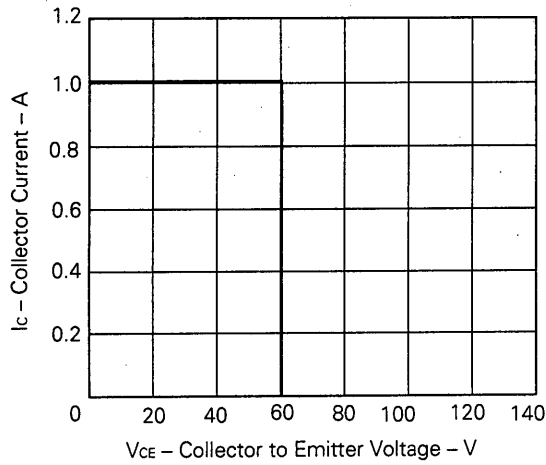
h_{FE} Classification

MARKING	M	L	K
h _{FE2}	2 000 to 5 000	4 000 to 10 000	8 000 to 30 000

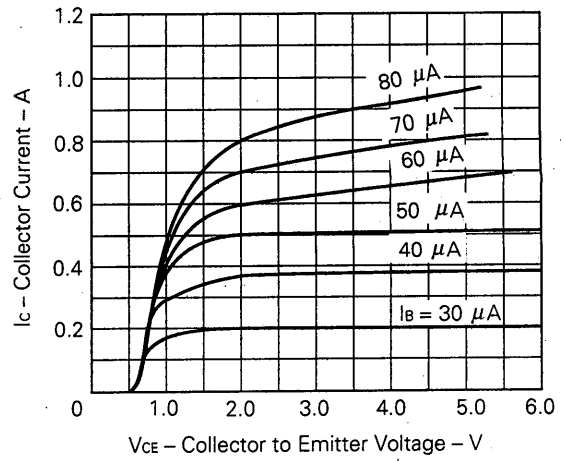
TYPICAL CHARACTERISTICS (T_a = 25 °C)



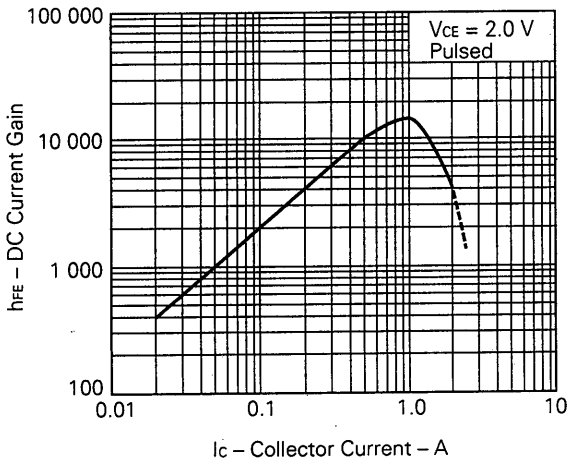
REVERSE BIAS SAFE OPERATING AREA



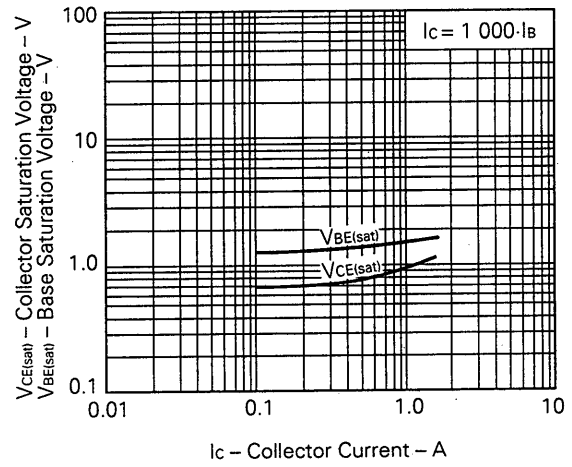
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



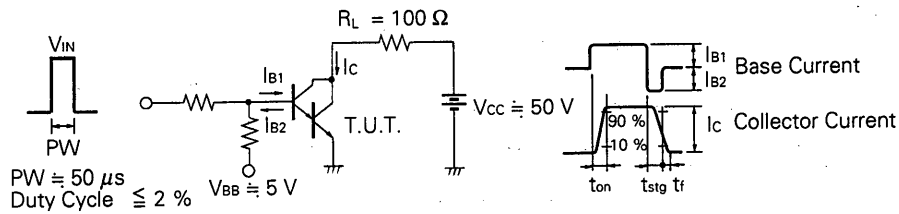
DC CURRENT GAIN vs. COLLECTOR CURRENT



BASE AND COLLECTOR SATURATION VOLTAGE vs. COLLECTOR CURRENT



SWITCHING TIME (t_{on} , t_{stg} , t_f) TEST CIRCUIT



Reference

Application note name	No.
Quality control of NEC semiconductors devices.	TEI-1202
Quality control guide of semiconductors devices.	MEI-1202
Assembly manual of semiconductors devices.	IEI-1207
Design of Push-Pull Type Switching Regulators (Basic)	TEB-1002
Design of Push-Pull Type Switching Regulators (Applications)	TEB-1003
Optimum Base Drive Conditions of Switching Power Transistors	TEB-1014

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Application examples recommended by NEC Corporation.

Standard: Computer, Office equipment, Communication equipment, Test and Measurement equipment, Machine tools, Industrial robots, Audio and Visual equipment, Other consumer products, etc.

Special: Automotive and Transportation equipment, Traffic control systems, Antidisaster systems, Anticrime systems, etc.